



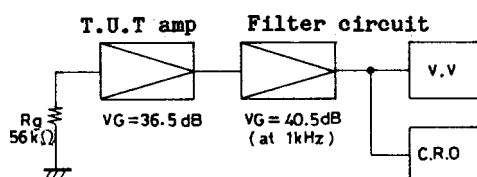
2SA1391/2SC3382

Low Noise AF Amp Applications

Features

- Adoption of FBET process.
- AF amp.
- Low-noise use.

Noise Test Circuit



() : 2SA1391

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)50	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)200	mA
Collector Current (Pulse)	I_{CP}		(-)400	mA
Collector Dissipation	P_C		400	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

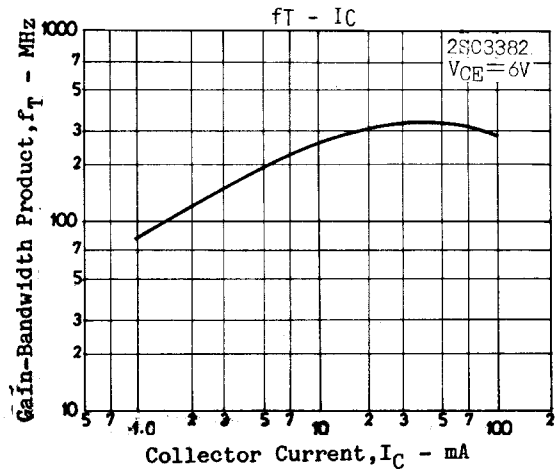
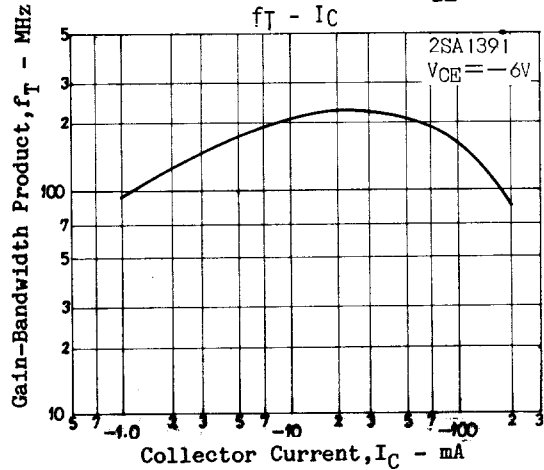
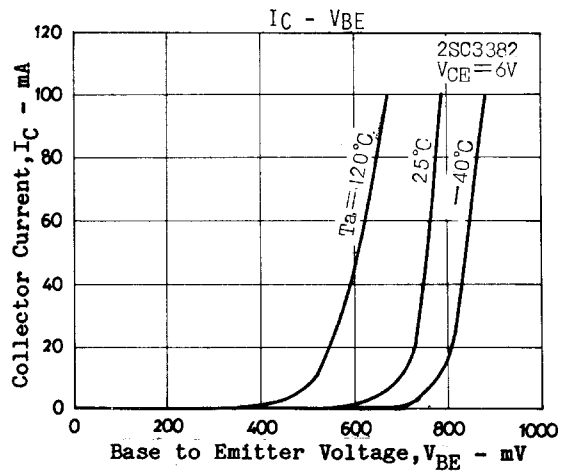
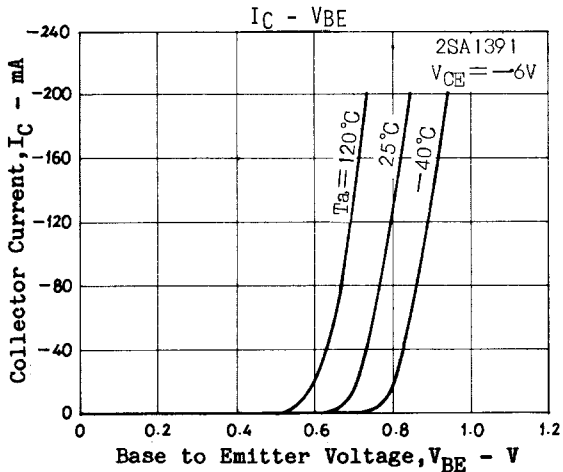
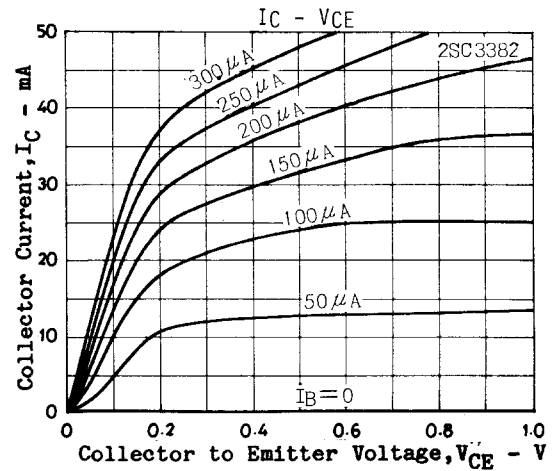
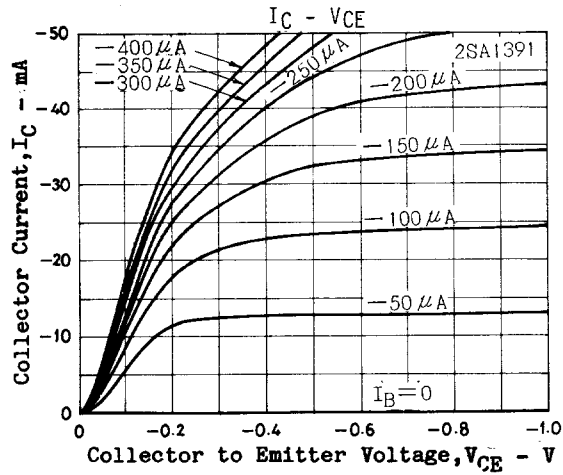
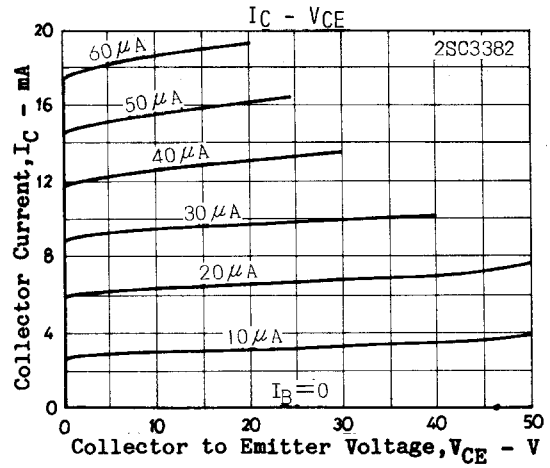
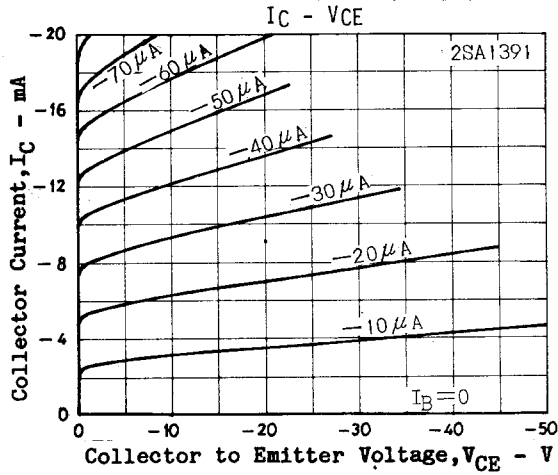
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$			(-)0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=(-)6V, I_C=(-)1mA$	100*		560*	
	h_{FE2}	$V_{CE}=(-)6V, I_C=(-)0.1mA$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)10mA$		250		MHz
				(200)		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$			(-)0.3	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$			(-)1.0	V
Output Capacitance	C_{ob}	$V_{CB}=(-)6V, f=1MHz$		2.7		pF
				(3.7)		pF
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10μA, I_E=0$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=∞$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10μA, I_C=0$	(-)6			V
Noise Level	$V_{NO(ave)}$	$V_{CC}=(-)30V, I_C=(-)1mA, R_g=56kΩ, V_G=77dB/1kHz$			40	mV
					(35)	mV
Noise Peak Level	$V_{NO(peak)}$	$V_{CC}=(-)30V, I_C=(-)1mA, R_g=56kΩ, V_G=77dB/1kHz$			280	mV
					(200)	mV

* : 2SA1391/2SC3382 are classified by 1mA h_{FE} as follows :

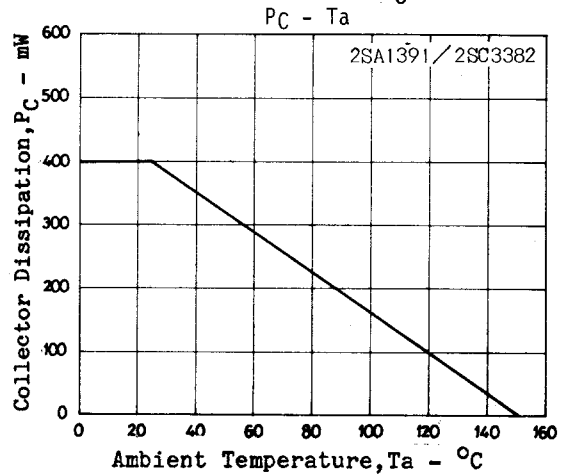
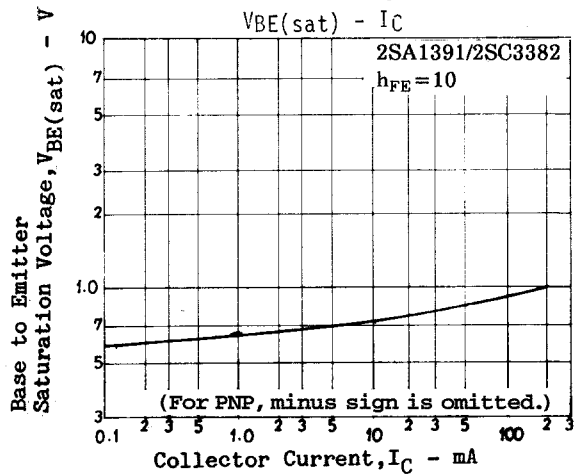
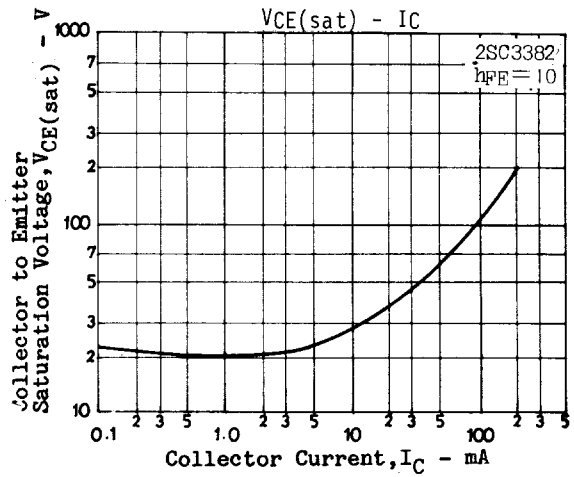
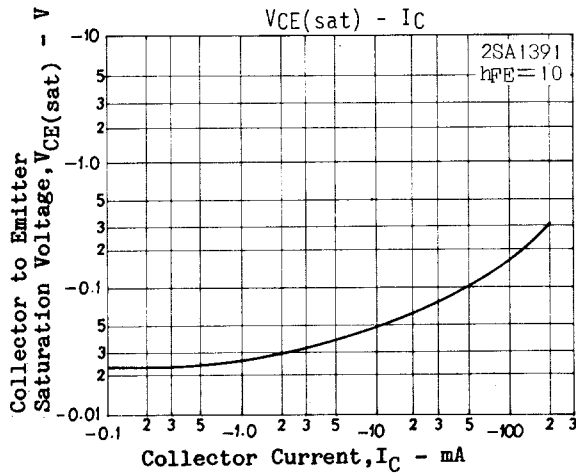
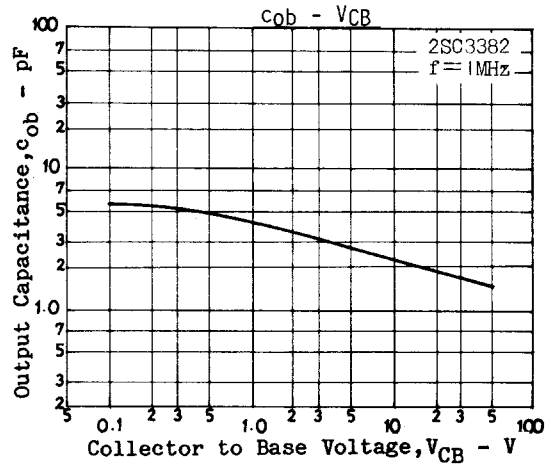
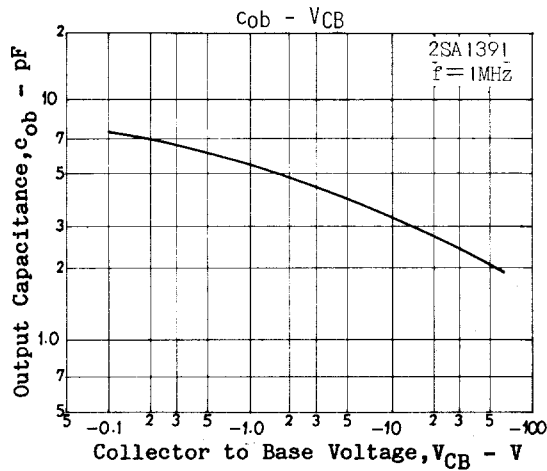
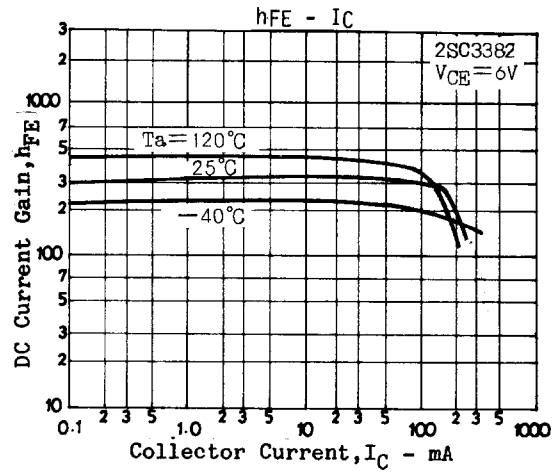
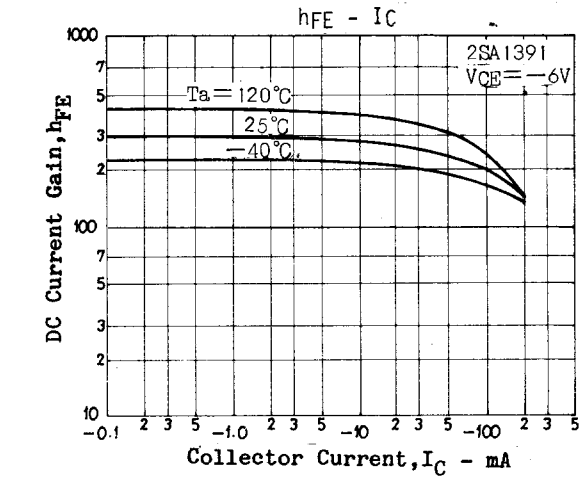
100	R	200	140	S	280	200	T	400	280	U	560
-----	---	-----	-----	---	-----	-----	---	-----	-----	---	-----

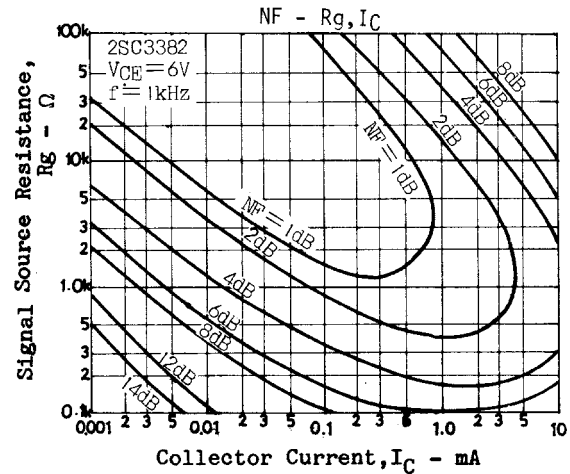
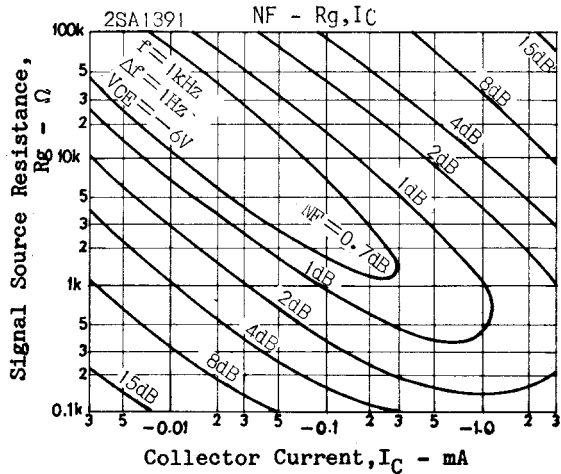
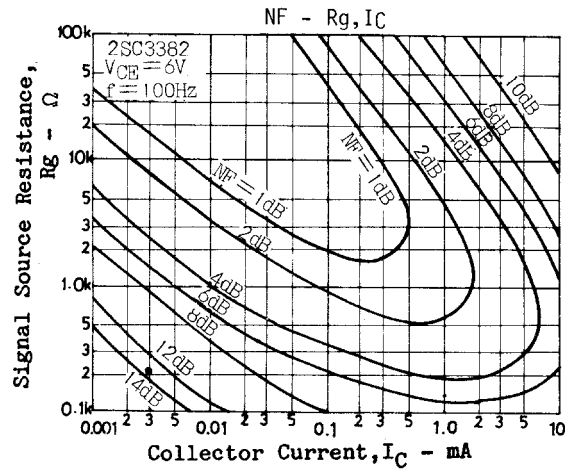
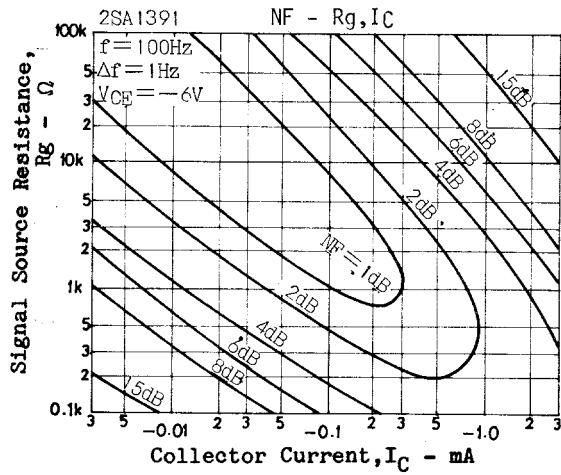
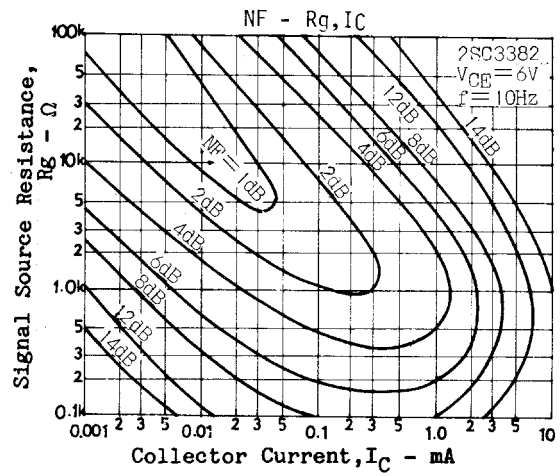
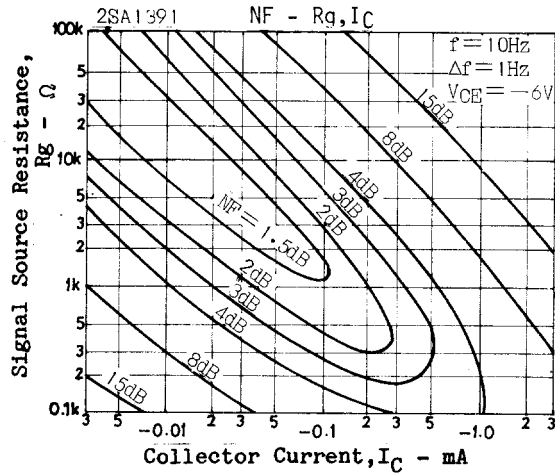
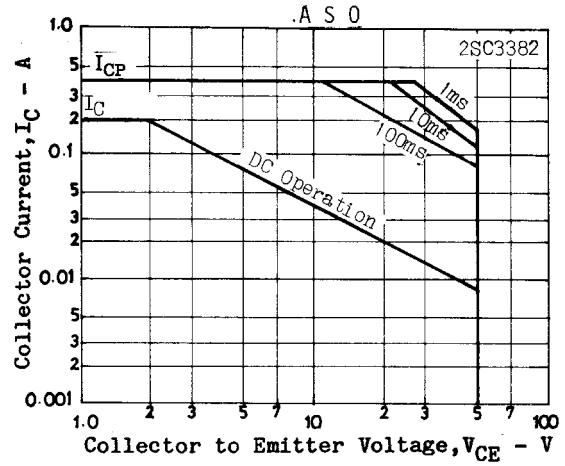
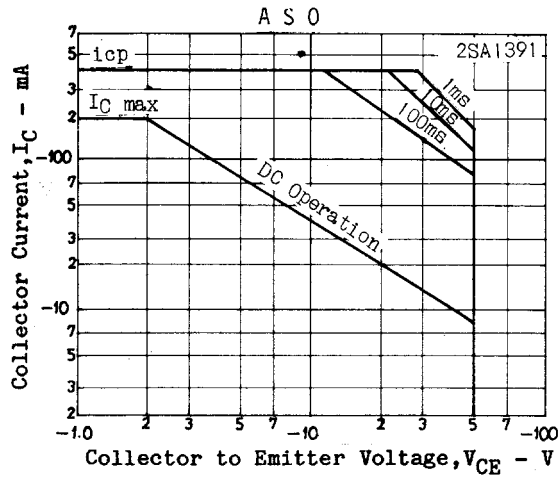
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

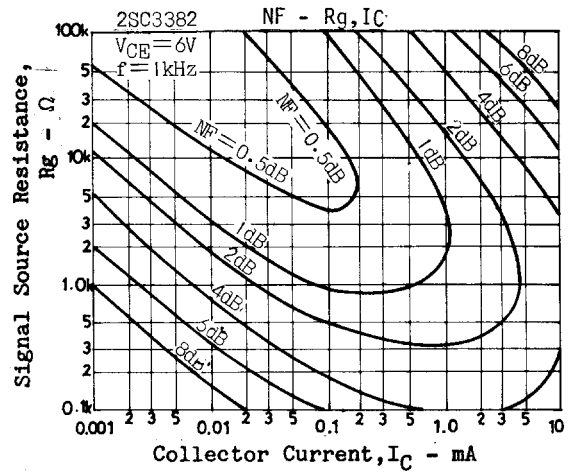
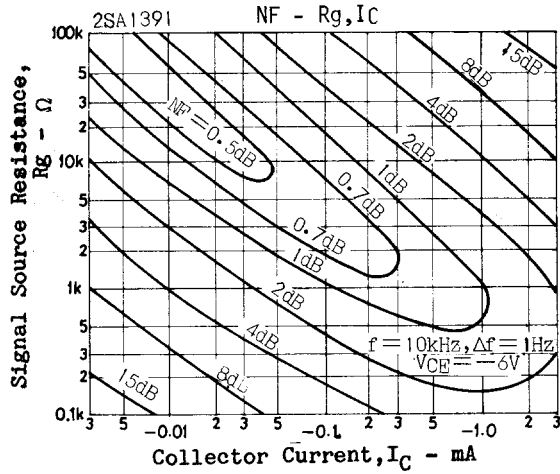


2SA1391/2SC3382





2SA1391/2SC3382



■ No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.

■ Anyone purchasing any products described or contained herein for an above-mentioned use shall:

- ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
- ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.

■ Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of July, 1998. Specifications and information herein are subject to change without notice.